

ABSTRACT

INORGANIC ANION EXCHANGER COMPOSED OF BISMUTH COMPOUND AND  
RESIN COMPOSITION FOR ELECTRONIC COMPONENT ENCAPSULATION

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USING THE SAME

Disclosed is a novel bismuth compound which is useful  
as an inorganic anion exchanger to be used for a  
semiconductor encapsulating material or the like.

10 Specifically disclosed is a novel bismuth compound  
represented by the formula (1) below, wherein the peak  
intensity at  $2\theta = 27.9^\circ - 28.1^\circ$  is 900-2000 cps and the peak  
intensity at  $2\theta = 8.45^\circ - 8.55^\circ$  is 100-800 cps in the powder  
X-ray diffraction pattern. This bismuth compound solves the  
15 problems of publicly known inorganic anion exchangers, and  
exhibits a high performance while being environmentally  
friendly.  $\text{Bi}(\text{OH})_x(\text{NO}_3)_y \cdot n\text{H}_2\text{O}$  (1) (In the formula (1), x  
represents a positive number not less than 2.5 and less  
than 3, y represents a positive number not more than 0.5,  
20 and  $x + y = 3$ , and n represents 0 or a positive number.)

(no accompanying figure)